

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 60188-776		SERIAL NO.	
				APPLICANT Masao SHINDO			
				FILING DATE February 20, 2004		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
M		US 5,856,003	01/05/1999	Chiu	_____		
		US					
		US					
		US					
		US					
		US					
		US					
		US					
		US					
		US					
		US					
		US					
		US					
		US					
		US					
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code ¹ -Number ¹ -Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
M		JP 59-50227	12/07/1984	TOSHIBA CORP		(Japan w/English Abstract)	
		JP P2001-291781A	10/19/2001	MATSUSHITA ELECTRIC IND CO LTD		(Japan w/English Abstract)	
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
M		Don H. LEE, et al., "Ion-Implanted Semiconductor Devices", Proceedings of the IEEE, pp.1241-1255, September 1974					
		EXAMINER			DATE CONSIDERED		
		H. J. J. J.			7/22/04		

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.